

Electronic Structures and Transport Properties of n-Type-Doped Indium Oxides

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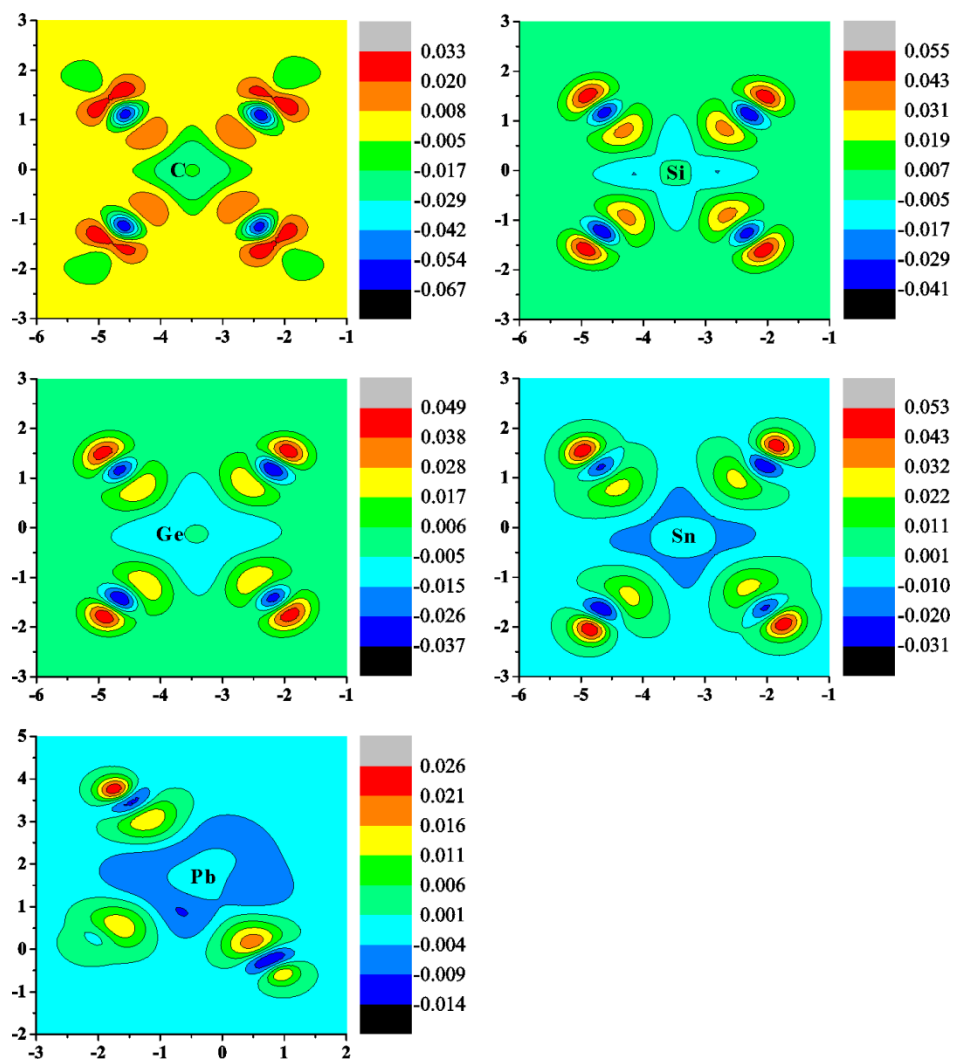


Figure S1. Charge density differences of In_2O_3 doped by group 14 elements. The charge difference is defined as $\Delta\rho = \rho_{\text{total}} - \rho_{\text{dopant}} - \rho_{\text{In}_2\text{O}_3}$. Here ρ_{total} , ρ_{dopant} and $\rho_{\text{In}_2\text{O}_3}$ refer to the charge density of doped system, single dopant atom and the rest In_2O_3 , respectively.

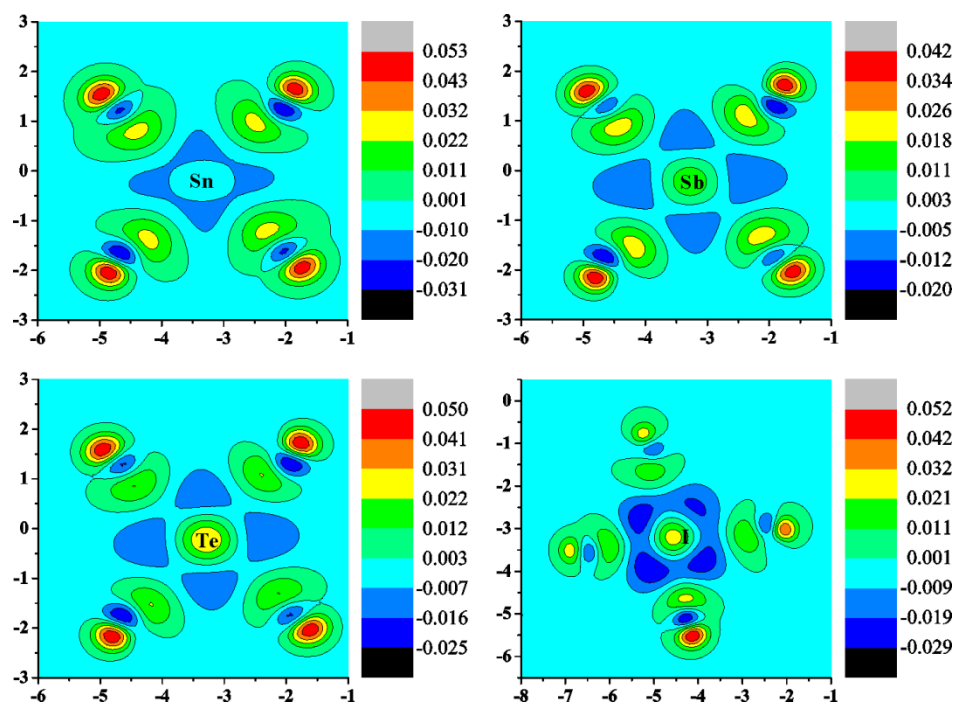


Figure S2. Charge density differences of In_2O_3 doped by Sn, Sb, Te and I.